

产品概览

NXH100B120H3Q0: Power Integrated Module, Dual Boost, 1200 V, 50 A IGBT + 1200 V, 20 A SiC Diode

欲看完整文档，请参阅数据表。

The NXH100B120H3Q0 is a power integrated module (PIM) containing a dual boost stage consisting of two 50A/1200V IGBTs, two 20A/1200V SiC diodes, and two 25A/1600V anti-parallel diodes for the IGBTs. Two additional 25A/1600V bypass rectifiers used for inrush current limit are included. An on-board thermistor is included.

特性

- IGBT Specifications: $V_{CE(SAT)} = 1.77\text{ V}$, $ESW = 2200\ \mu\text{J}$
- 25 A / 1600 V Bypass and Anti-parallel Diodes
- SiC Rectifier Specification: $V_F = 1.44\text{ V}$
- Solder pin and press-fit pin options available

优势

- Fast IGBT with low $V_{CE(SAT)}$ for high efficiency
- Low V_F bypass diodes for excellent efficiency in bypass mode
- SiC Diode for high speed switching
- Flexible mounting

应用

- MPPT Boost Stage
- Battery Charger Boost Stage

终端产品

- Solar Inverters
- Energy Storage Systems

器件电气规格

产品	Pricing (\$/Unit)	Compliance	Status	Configuration	V_{BR} Max (V)	Rated Current (A)	$V_{CE(sat)}$ Typ (V)	V_F Typ (V)	Package Type
NXH100B120H3Q0PG	30.6659	Pb-free Halide free	Active	Dual Boost	1200	50	1.77	1.44	PIM22 55x32.5 (PRESSFIT PIN)
NXH100B120H3Q0PT G	38.6657	Pb-free Halide free	Active	Dual Boost	1200	50	1.77	1.44	PIM22 55x32.5 (PRESSFIT PIN)
NXH100B120H3Q0SG	30.6659	Pb-free Halide free	Active	Dual Boost	1200	50	1.77	1.44	Q0
NXH100B120H3Q0ST G	38.6657	Pb-free Halide free	Active	Dual Boost	1200	50	1.77	1.44	Q0

欲了解更多信息，请联系您当地的销售支援 www.onsemi.cn。

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